4. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, in accordance with ~~claims 1, 2, or~~ claim 3, wherein the electroconductive region ~~(8b)~~ substantially extends over the entire breadth ~~(b)~~ of the compensation structure ~~(5)~~.

5. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to ~~any of the preceding claims~~ claim 4, comprising a plurality of, in particular more than 10, 100, 1,000 or 10,000, electroconductive regions ~~(8a, 8b)~~ that are electrically connected with the product field area ~~(6a)~~.

6. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to claim 5, wherein – viewed from the product field area ~~(6a)~~ – the electroconductive regions ~~(8a, 8b)~~ each extend path-shaped outwardly.

7. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, in accordance with ~~claims 5 or~~ claim 6, wherein the plurality of electrical regions ~~(8a, 8b)~~ form a grid structure.

8. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to ~~any of the preceding claims~~ claim 7, wherein the electroconductive region(s) ~~(8a, 8b)~~ is (are) designed of chrome.

9. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to ~~any of claims 5 to~~ claim 8, wherein electrically non-conductive regions ~~(9a, 9b)~~ are positioned between the electroconductive regions ~~(8a, 8b)~~.

10. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to claim 9, wherein at least two non-conductive regions ~~(9a, 9b)~~ have differing depths (t_0, t_1).

11. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to claim 10, wherein a respective plurality of electrically non-conductive regions ~~(9a, 9b)~~ that are positioned side by side, in particular more than 3, 50, or 500 electrically non-conductive regions ~~(9a, 9b)~~ that are positioned side by side, alternatingly have respectively differing depths (t_0, t_1).

12. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to ~~any of claims 9 to~~ claim 11, wherein the electrically non-conductive regions ~~(9a, 9b)~~ are designed of quartz.

13. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to ~~any of claims 9 to~~ claim 12, wherein the electrically non-conductive regions ~~(9a, 9b)~~ that are positioned between the electroconductive regions ~~(8a, 8b)~~ have a rectangular, in particular square, or a round or oval, respectively, cross-section.

14. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to ~~any of the preceding claims~~ claim 13, wherein the compensation structure ~~(5)~~ is formed around the at least one, or around the at least one and around further, product field areas ~~(6a, 6b)~~.

15. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to claim 14, wherein the compensation structure ~~(5)~~ is frame-shaped.

16. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to ~~any of the preceding claims~~ claim 15, said mask comprising a quartz and/or a chrome layer (2, 3).

17. (currently amended) The mask ~~(1)~~, in particular photomask, for the production of semiconductor devices, according to ~~any of the preceding claims~~ claim 16, wherein the mask ~~(1)~~ is an alternating phase shift mask, or a chromeless or a CPL (chromeless phase etch lithography) mask, respectively.

18. (currently amended) A method for the production of masks, in particular for the production of alternating phase shift masks, or of chromeless phase shift masks or phase shift masks structured by quartz etching, respectively, comprising at least one product field area ~~(6a)~~ and a compensation structure ~~(5)~~ positioned outside the product field area ~~(6a)~~, characterized in that the method comprises the step: providing of the compensation structure ~~(5)~~ with at least one electroconductive region ~~(8b)~~ which is – in the finished state of the mask – electrically connected with the product field area ~~(6a)~~.